

out with the above electron beam irradiation, and the at least one parameters is changed during these treatments in a chamber that is the same as a reactor chamber for carrying out the electron beam irradiation treatment.--

2. Please replace the paragraph beginning on page 26, line 24, and ending on page 27, line 3, with the following new paragraph:

--Further, in the insulation film formed by process C, there appears a large peak caused by H₂O bonding in the vicinity of a wave number of 3500 cm⁻¹ and Si-OH bonding in a vicinity of a wave number of 980 cm⁻¹, but in the insulation films formed by the process of present embodiment and process A, almost no peak appears in the vicinity of the above wave number.--

3. Please replace the paragraph beginning on page 27, line 5, with the following new paragraph:

--From these facts, in the case process C, it is considered that a sufficient dehydration reaction is not carried out, and a number of Si-OH bonding and H₂O remains in the insulation film.--

4. Please replace the paragraph beginning on page 27, line 20, and ending on page 28, line 10, with the following new paragraph:

--On the other hand, in the insulation film formed by the process of the present embodiment, there appears neither a peak caused by H₂O bonding in the vicinity of the wavelength of 3500 cm⁻¹ nor a peak caused by Si-OH bonding in the vicinity of the wavelength

FINNEGAN
HENDERSON
FARABOW
GARRETT &
DUNNER LLP

1300 I Street, NW
Washington, DC 20005
202.408.4000
Fax 202.408.4400
www.finnegan.com